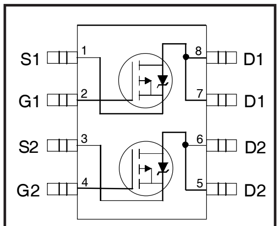
International
IOR Rectifier

PD - 96107A

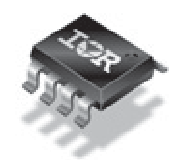
IRF7314QPbF

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ max	I_D
-20V	0.058@V_{GS} = -4.5V	-5.2A
	0.098@V_{GS} = -2.7V	-4.42A



Top View



SO-8

Benefits

- Advanced Process Technology
- Dual P-Channel MOSFET
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free

Description

These HEXFET ® Power MOSFET's in a Dual SO-8 package utilize the lastest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these HEXFET Power MOSFET's are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

The 175°C rating for the SO-8 package provides improved thermal performance with increased safe operating area and dual MOSFET die capability make it ideal in a variety of power applications. This dual, surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	-20	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	-5.2	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	-4.3	
I_{DM}	Pulsed Drain Current①	-43	
P_D @T_A = 25°C	Maximum Power Dissipation③	2.4	W
P_D @T_A = 70°C	Maximum Power Dissipation③	1.7	W
	Linear Derating Factor	16	mW/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
E_{AS}	Single Pulse Avalanche Energy②	610	mJ
I_{AR}	Avalanche Current①	-5.2	A
E_{AR}	Repetitive Avalanche Energy	See Fig.14, 15, 16	mJ
T_J , T_{STG}	Junction and Storage Temperature Range	-55 to + 175	°C

Thermal Resistance

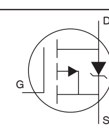
	Parameter Max.	Units	
$R_{\theta JA}$	Maximum Junction-to-Ambient ③	62.5	°C/W

08/02/10

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	–––	–––	V	V_{GS} = 0V, I_D = -250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.009	–––	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	0.049	0.058	Ω	V_{GS} = -4.5V, I_D = -5.2A ②
		–––	0.082	0.098		V_{GS} = -2.7V, I_D = -4.42A ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.7	–––	–––	V	V_{DS} = V_{GS}, I_D = -250μA
g_{fs}	Forward Transconductance	6.8	–––	–––	S	V_{DS} = 10V, I_D = -5.2A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	-1.0	μA	V_{DS} = -16V, V_{GS} = 0V
		–––	–––	-25		V_{DS} = -16V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	-100	nA	V_{GS} = -12V
	Gate-to-Source Reverse Leakage	–––	–––	100		V_{GS} = 12V
Q_g	Total Gate Charge	–––	19	29	nC	I_D = -5.2A
Q_{gs}	Gate-to-Source Charge	–––	2.1	3.2		V_{DS} = -16V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	9.3	14		V_{GS} = -4.5V
$t_{d(on)}$	Turn-On Delay Time	–––	18	–––	ns	V_{DD} = -10V
t_r	Rise Time	–––	26	–––		I_D = -1.0A
$t_{d(off)}$	Turn-Off Delay Time	–––	41	–––		R_G = 6.0Ω
t_f	Fall Time	–––	38	–––		V_{GS} = -4.5V ②
C_{iss}	Input Capacitance	–––	913	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	512	–––		V_{DS} = -15V
C_{rss}	Reverse Transfer Capacitance	–––	260	–––		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	-3.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	-43		
V_{SD}	Diode Forward Voltage	–––	–––	-1.0	V	T_J = 25°C, I_S = -3.0A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	–––	44	66	ns	T_J = 25°C, I_F = -3.0A
Q_{rr}	Reverse Recovery Charge	–––	54	81	nC	di/dt = -100A/μs ②

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 45mH R_G = 25Ω, I_{AS} = -5.2A.

③ Surface mounted on FR-4 board, t ≤ 10sec.

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

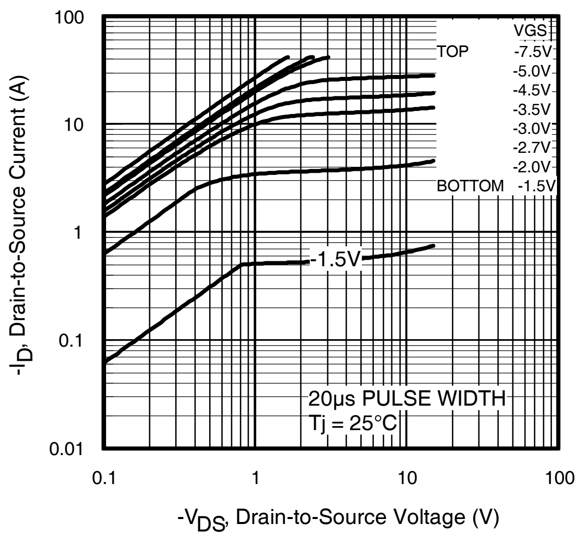


Fig 1. Typical Output Characteristics

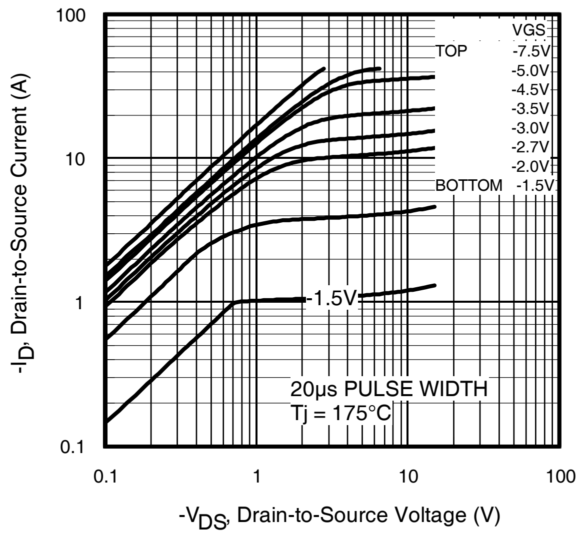


Fig 2. Typical Output Characteristics

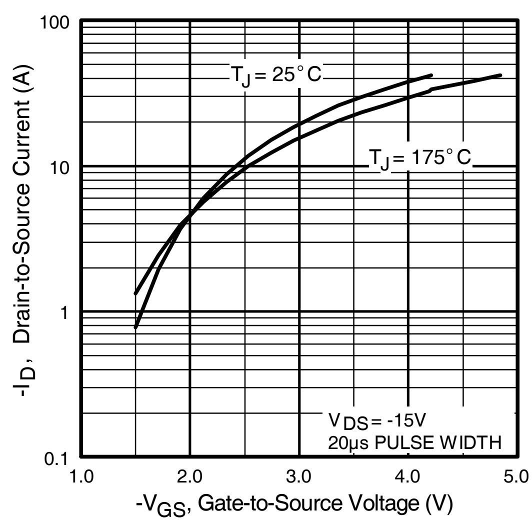


Fig 3. Typical Transfer Characteristics

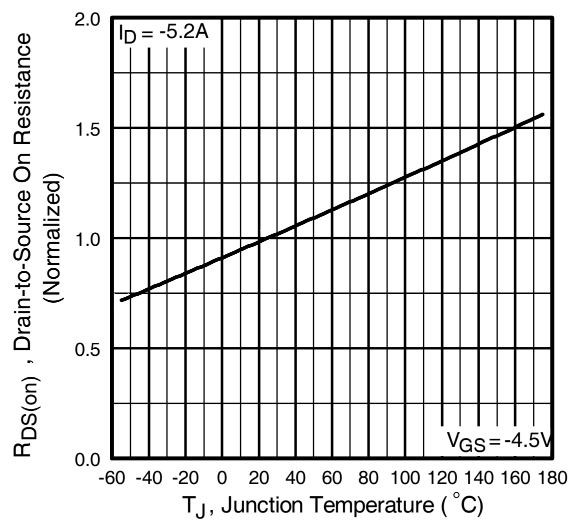


Fig 4. Normalized On-Resistance Vs. Temperature

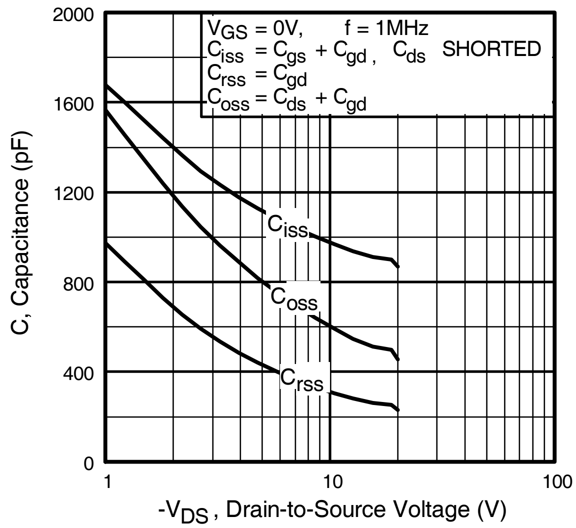


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

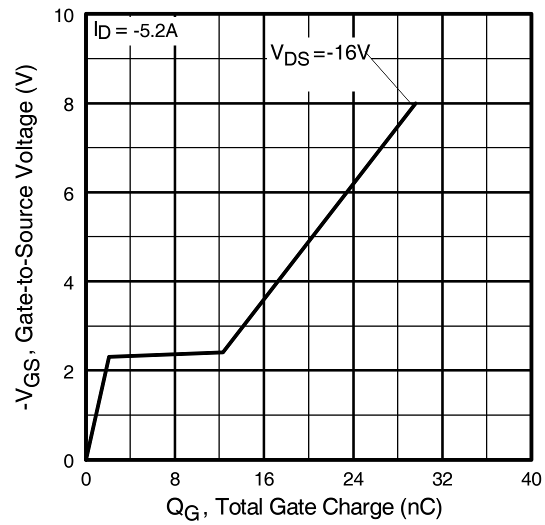


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

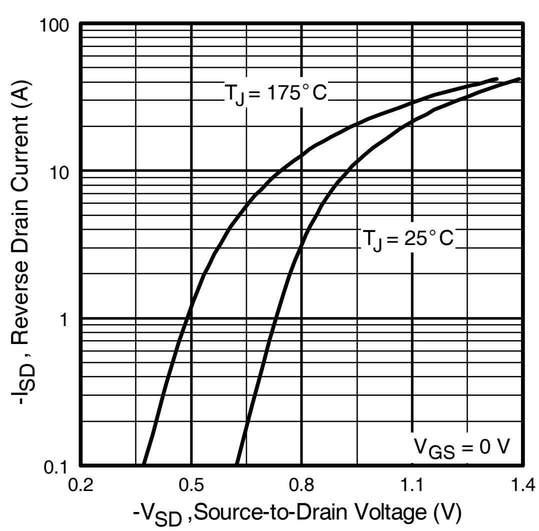


Fig 7. Typical Source-Drain Diode Forward Voltage

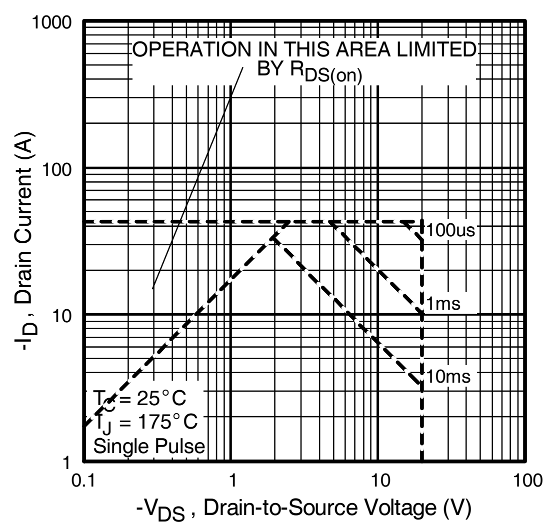


Fig 8. Maximum Safe Operating Area

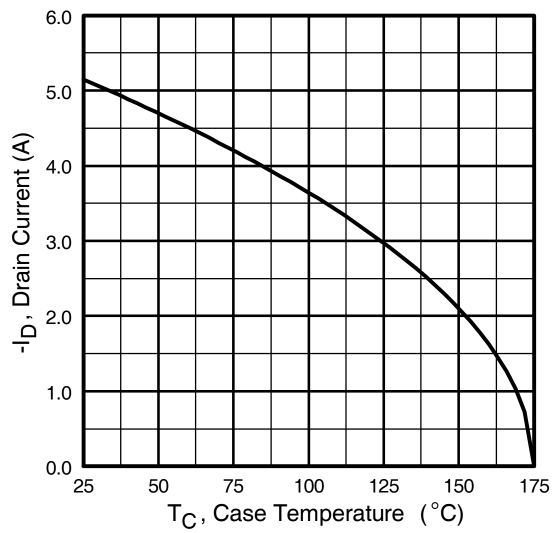


Fig 9. Maximum Drain Current Vs. Case Temperature

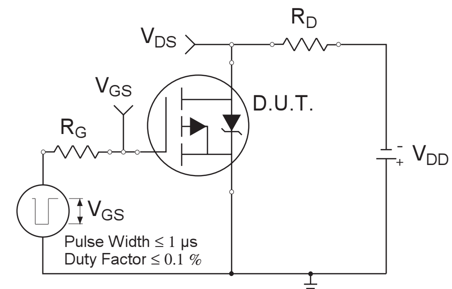


Fig 10a. Switching Time Test Circuit

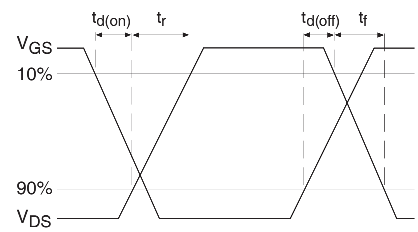


Fig 10b. Switching Time Waveforms

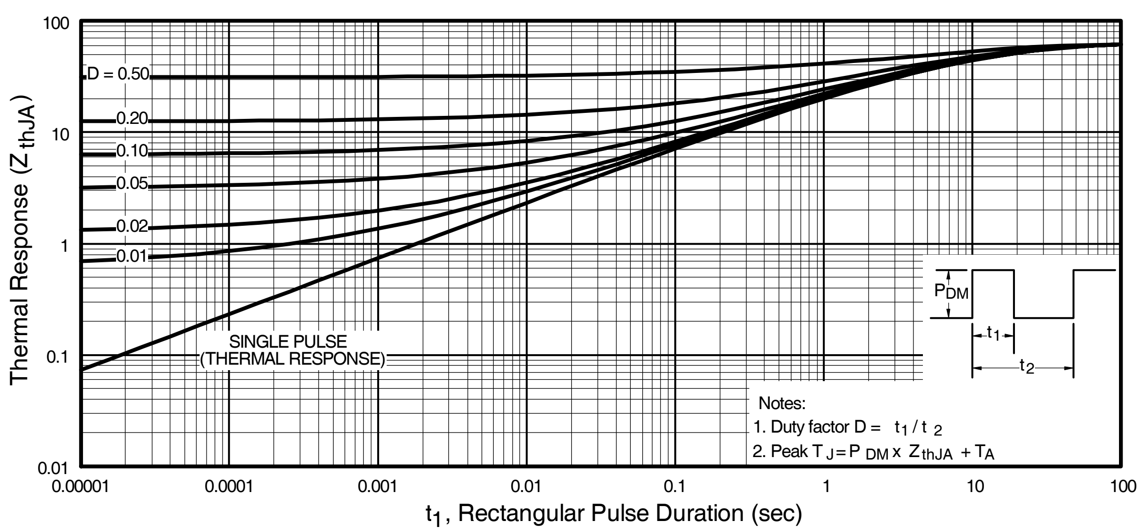


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

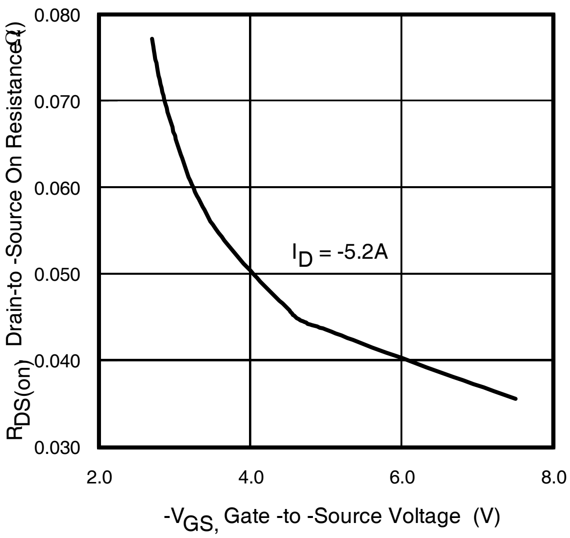


Fig 11. Typical On-Resistance Vs. Gate Voltage

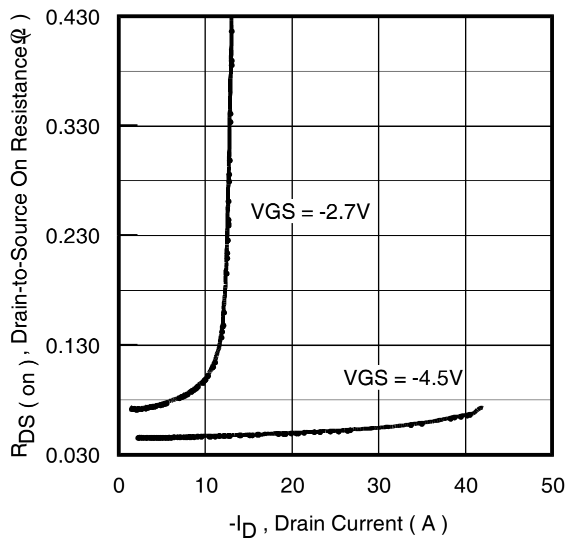


Fig 12. Typical On-Resistance Vs. Drain Current

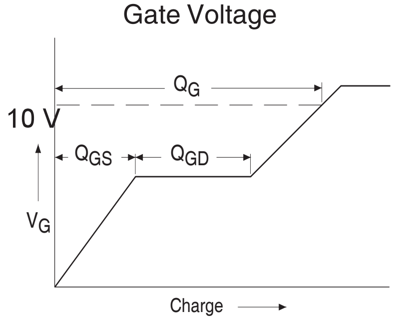


Fig 13a. Basic Gate Charge Waveform

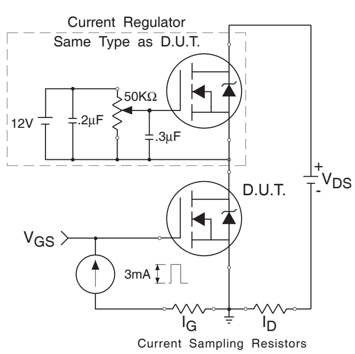


Fig 13b. Gate Charge Test Circuit

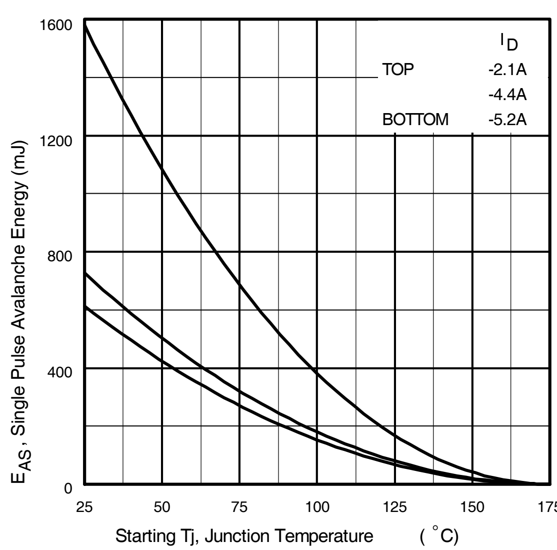


Fig 14. Maximum Avalanche Energy Vs. Drain Current

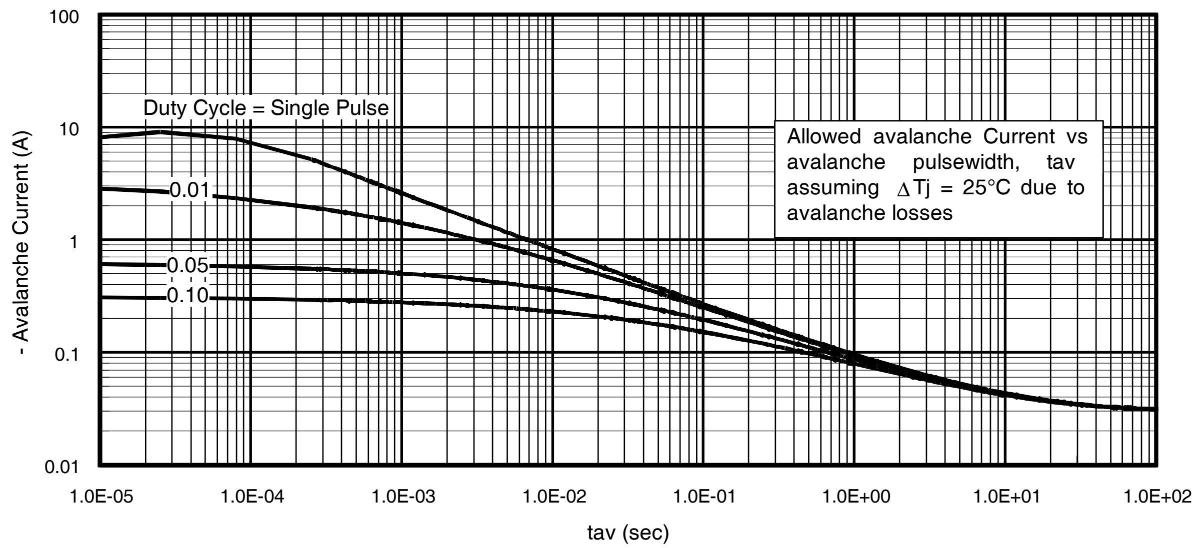


Fig 15. Typical Avalanche Current Vs.Pulsewidth

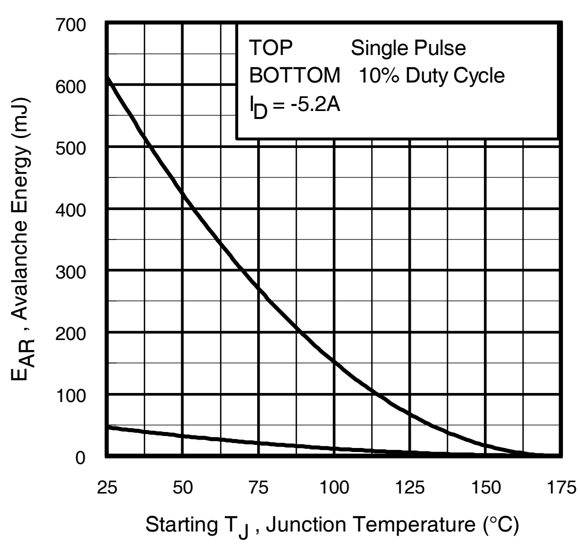


Fig 16. Maximum Avalanche Energy Vs. Temperature

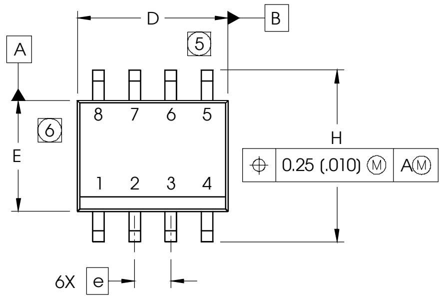
Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

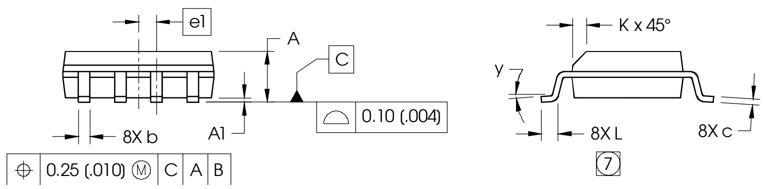
$$P_{D\ (ave)} = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

SO-8 Package Outline

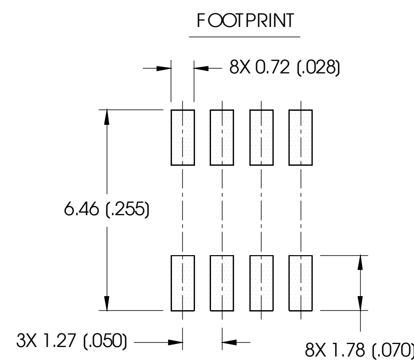
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

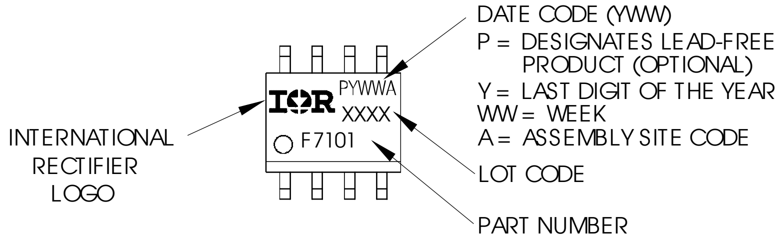


NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



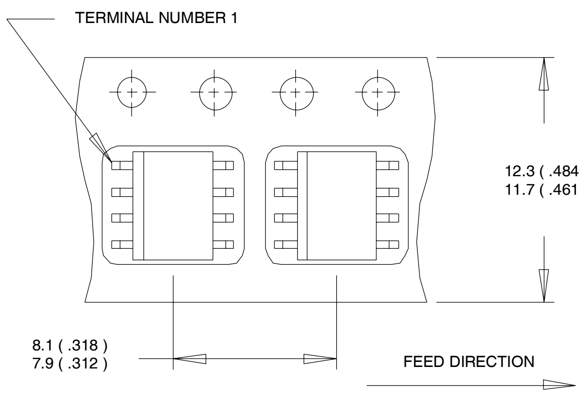
Notes:

1. For an Automotive Qualified version of this part please seehttp://www.irf.com/product-info/auto/

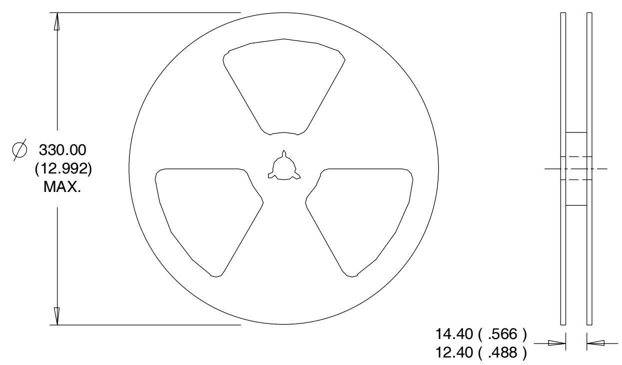
2. For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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